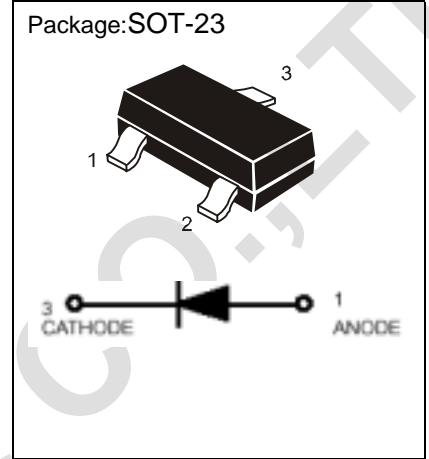


MONOLITHIC DUAL SWITCHING DIODE

ABSOLUTE MAXIMUM RATINGS at Ta=25°C

Characteristic	Symbol	Rating	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	200	Vdc
Peak Forward surge Current	$I_{FM}(\text{surge})$	500	mAdc
Total Device Dissipation FR-5 Board(Note)	P_D	225	mW
Derate above 25°C		1.8	mW/°C
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55-150	°C



ELECTRICAL CHARACTERISTICS at Ta=25°C

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage($I_R=100\mu\text{Adc}$)	$V_{(BR)}$	75		Vdc
Reverse Voltage Leakage Current ($V_R=50\text{Vdc}$)	I_R		0.1	μAdc
Diode Capacitance($V_R=0$ f=1.0MHz)	C_T			PF
Forward Voltage ($I_F=1.0\text{mAdc}$) ($I_F=100\text{mAdc}$)	V_F	0.55 0.85	0.7 1.1	Vdc
Reverse Recovery Time($I_F=I_R=10\text{mAdc}$)	T_{rr}		2.5	ns

Note:FR-5=1.0 x 0.75 x 0.062in

DEVICE MARKING:

MMBD6050LT1=5A